



2-Line Ultra Low Capacitance Uni-directional TVS Diode

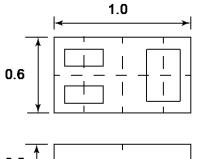
Description

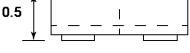
The PESDR0532P1 is an uni-directional TVS diode. utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The PESDR0532P1 has an ultra-low capacitance with a typical value at 0.6pF, and complies with the IEC 61000-4-2 (ESD) with ±15kV air and ±8kV contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size, ultra-low capacitance and high ESD surge protection make PESDR0532P1 an ideal choice to protect cell phone, digital visual interfaces and other high speed ports.

Features

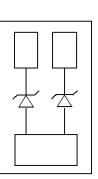
- Ultra small package: 1.0x0.6x0.5mm
- Ultra low capacitance: 0.6pF typical
- Ultra low leakage: nA level
- Operating voltage: 5V
- Low clamping voltage
- 3-pin leadless package
- Up to 2-line protects
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 Air discharge: ±15kV
 Contact discharge: ±8kV
 - IEC 61000-4-5 (Lightning) 3.5A (8/20µs)
- RoHS Compliant

Dimensions and Pin Configuration





Package Dimensions



Circuit and Pin Schematic

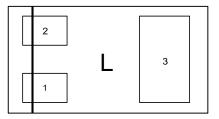
Mechanical Characteristics

- Package: DFN1006-3 (1.0×0.6×0.5mm)
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB 2.0 and 3.0 Ports
- HDMI 1.3 and 1.4
- Digital Video Interface (DVI)
- PCI Express and Serial SATA Ports
- Notebook Computer
- IEEE 1394

Marking Information



L = Device Marking Code Bar denotes cathode

Ordering Information

Part Number	Packaging	Reel Size
PESDR0532P1	10000/Tape & Reel	7 inch



Absolute Maximum Ratings (TA=25°C unless otherwise specified)

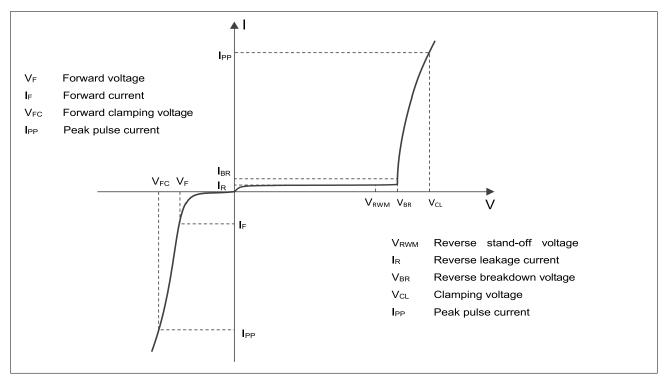
Parameter	Symbol	Value	Unit	
Peak Pulse Power (8/20µs)	Р _{РК} 53		W	
Peak Pulse Current (8/20µs)	Ірр	3.5	А	
ESD per IEC 61000-4-2 (Air)	V	±15		
ESD per IEC 61000-4-2 (Contact)	Vesd	±8	kV	
Lead temperature	TL	260	Ċ	
Operating Temperature Range	Тор	-40 ~ +85	°C	
Storage Temperature Range	Тѕтс	-55 ~ +150	°C	

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Мах	Unit	Test Condition
Boyeree Werking Veltage	Vrwm			5.0	V	Pin 1 or Pin 2 to Pin 3 and
Reverse Working Voltage	VRWM			5.0	v	between Pin 1 and Pin 2
Breakdown Voltage	V _{BR}	6.0	8.5		V	$I_T = 1 \text{ mA}$, Pin 1 or Pin 2 to Pin 3
Breakdown vollage	VBR	0.0	0.5		v	and between Pin 1 and Pin 2
Roverse Leakage Current	IR		0.1	0.5	μA	V_{RWM} =5V, Pin 1 or Pin 2 to Pin
Reverse Leakage Current	IR		0.1	0.5		3 and between Pin 1 and Pin 2
	Vc			10	V	I _{PP} = 1A (8/20µs pulse), Pin 1
Clamping Voltage	VC			10		or Pin 2 to Pin 3
	Vc			15	V	I _{PP} = 3.5A (8/20µs pulse), Pin 1
Clamping Voltage	VC			15	v	or Pin 2 to Pin 3
Junction Conscitance	C.		0.25	0.4	pF	$V_R = 0V$, f = 1MHz, Pin 1 to Pin
Junction Capacitance	CJ		0.25	0.4		2
Junction Consoltance	ction Capacitance CJ 0.5 0.8 pF	۳E	$V_R = 0V$, f = 1MHz, Pin 1 or Pin			
Junction Capacitance		рг	2 to Pin 3			



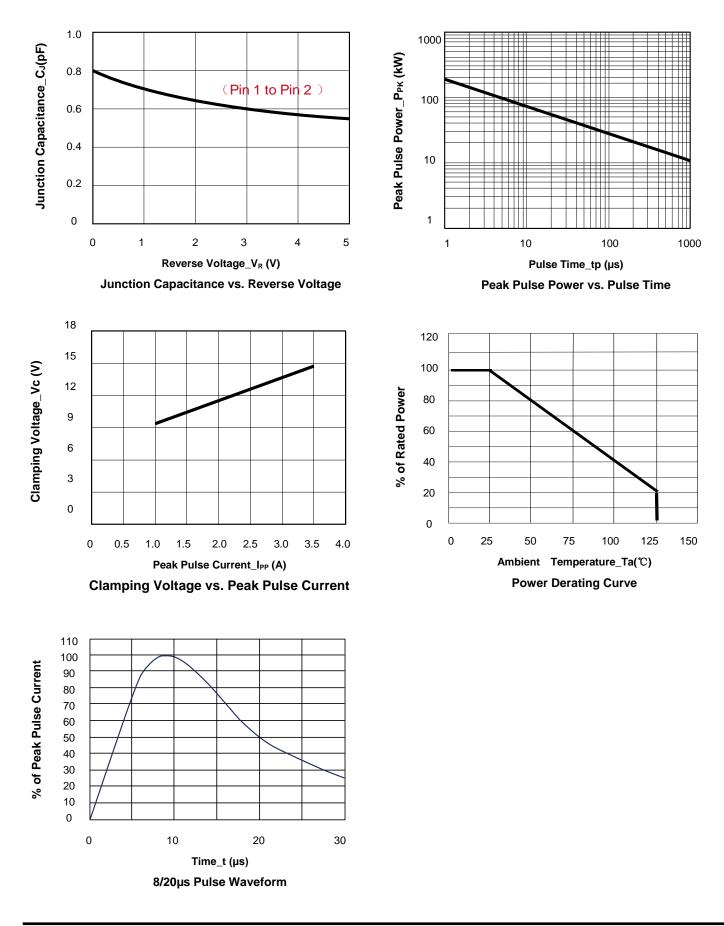
<u>Electrical characteristics ($T_A = 25^{\circ}$, unless otherwise noted)</u>



Definitions of electrical characteristics



Typical Performance Characteristics (T_A=25°C unless otherwise Specified)

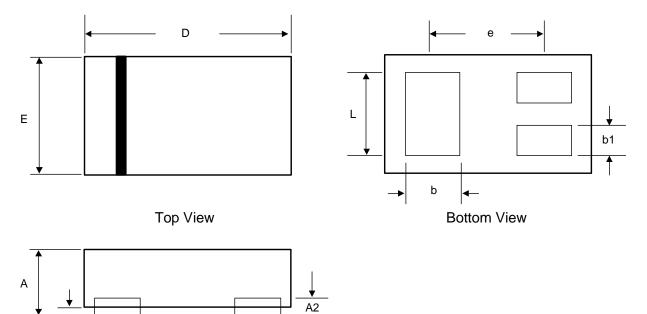




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DFN1006-3 Package Outline Drawing

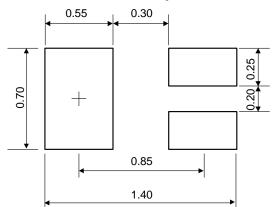


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Side View

Symbol	Dimensions in Millimeters			
	Min.	Тур.	Max.	
А	0.340	0.450	0.550	
A1	0.000	0.020	0.050	
A2	0.125 Ref.			
D	0.950	1.000	1.075	
E	0.490	0.600	0.675	
b	0.200	0.250	0.300	
b1	0.100	0.150	0.200	
L	0.450	0.500	0.550	
е	0.650 BSC			

Recommended PCB Layout (Unit: mm)



Notes:

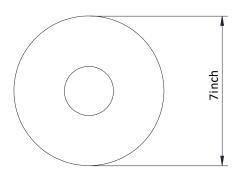
This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.



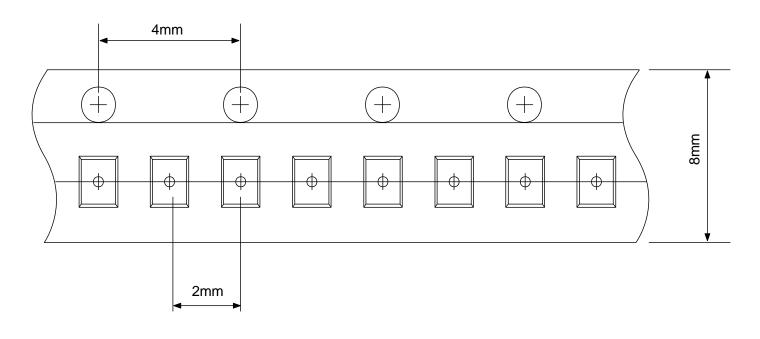


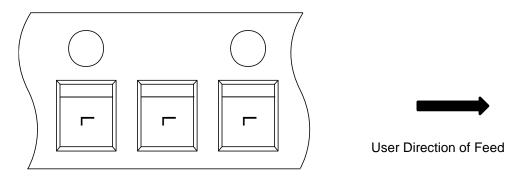
TAPE AND REEL INFORMATION

Reel Dimensions



Tape Dimensions







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